



DMTH6009LPS-13 Information



For Reference Only

Part Number DMTH6009LPS-13
Manufacturer Diodes Incorporated

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET BVDSS 41V 60V POWERDI5060

Package 8-PowerTDFN

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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DMTH6009LPS-13 Specifications

Manufacturer Part Number DMTH6009LPS-13 Manufacturer Diodes Incorporated Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-PowerTDFN Series Automotive, AEC-Q101 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 11.76A (Ta), 89.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 15.6nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1925pF @ 30V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 2.8W (Ta), 136W (Tc) Rds On (Max) @ Id, Vgs 10 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerDI5060-8 Package / Case 8-PowerTDFN		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-PowerTDFN Series Automotive, AEC-Q101 FET Type N-Channel Technology MOSFET (Metal Oxide) Train to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 11.76A (Ta), 89.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Queen Charge (Qg) (Max) @ Vgs 15.6nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1925pF @ 30V Vgs (Max) ##OVERTY	Manufacturer Part Number	DMTH6009LPS-13
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SeriesAutomotive, AEC-Q101FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C11.76A (Ta), 89.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs15.6nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1925pF @ 30VVgs (Max)±16VFET Feature-Power Dissipation (Max)2.8W (Ta), 136W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 20A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerDI5060-8Package / Case8-PowerTDFN		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C11.76A (Ta), 89.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs15.6nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1925pF @ 30VVgs (Max)±16VFET Feature-Power Dissipation (Max)2.8W (Ta), 136W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 20A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerDI5060-8Package / Case8-PowerTDFN	Package	8-PowerTDFN
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C11.76A (Ta), 89.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs15.6nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1925pF @ 30VVgs (Max)±16VFET Feature-Power Dissipation (Max)2.8W (Ta), 136W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 20A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerDI5060-8Package / Case8-PowerTDFN	Series	Automotive, AEC-Q101
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C11.76A (Ta), 89.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs15.6nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1925pF @ 30VVgs (Max)±16VFET Feature-Power Dissipation (Max)2.8W (Ta), 136W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 20A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerDI5060-8Package / Case8-PowerTDFN	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 mOhm @ 20A, 10V Operating Temperature Supplier Device Package Package / Case 11.76A (Ta), 89.5A (Tc) 12.6V 2.50µA 15.6nC @ 4.5V 1925pF @ 30V 2.8W (Ta), 136W (Tc) 10 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerDI5060-8 8-PowerTDFN	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs15.6nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1925pF @ 30VVgs (Max)±16VFET Feature-Power Dissipation (Max)2.8W (Ta), 136W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 20A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerDI5060-8Package / Case8-PowerTDFN	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 2V @ 250μA 15.6nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1925pF @ 30V ±16V	Current - Continuous Drain (Id) @ 25°C	11.76A (Ta), 89.5A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1925pF @ 30V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-PowerTDFN	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-PowerTDFN	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max)±16VFET Feature-Power Dissipation (Max)2.8W (Ta), 136W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 20A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerDI5060-8Package / Case8-PowerTDFN	Gate Charge (Qg) (Max) @ Vgs	15.6nC @ 4.5V
FET Feature - Power Dissipation (Max) 2.8W (Ta), 136W (Tc) Rds On (Max) @ Id, Vgs 10 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerDI5060-8 Package / Case 8-PowerTDFN	Input Capacitance (Ciss) (Max) @ Vds	1925pF @ 30V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-PowerTDFN	Vgs (Max)	±16V
Rds On (Max) @ Id, Vgs10 mOhm @ 20A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerDI5060-8Package / Case8-PowerTDFN	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerDI5060-8 Package / Case 8-PowerTDFN	Power Dissipation (Max)	2.8W (Ta), 136W (Tc)
Mounting Type Surface Mount Supplier Device Package PowerDI5060-8 Package / Case 8-PowerTDFN	Rds On (Max) @ Id, Vgs	10 mOhm @ 20A, 10V
Supplier Device Package PowerDI5060-8 Package / Case 8-PowerTDFN	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case 8-PowerTDFN	Mounting Type	Surface Mount
	Supplier Device Package	PowerDI5060-8
Report errors?	Package / Case	8-PowerTDFN
		Report errors?

DMTH6009LPS-13 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

DMTH6009LPS-13 Payment Methods



















DMTH6009LPS-13 Shipping Methods













If you have any question about DMTH6009LPS-13, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com